IN THE CLAIMS:

Please amend claims 32, 34, 36-38, and 40 as follows:

32. (Amended) A polishing pad assembly for polishing a semiconductor wafer, said assembly comprising:

a belt forming a closed loop; [and]

at least one non-fixed abrasive chemical mechanical planarization polishing pad mounted on the belt, the non-fixed abrasive chemical mechanical planarization polishing pad configured to [adapted to] receive a polishing slurry, wherein the non-fixed abrasive chemical mechanical planarization polishing pad polishes a surface of the semiconductor wafer with the polishing slurry; and,

wherein said belt is formed of metal.

34. (Amended) A polishing pad assembly for polishing a semiconductor wafer, said assembly comprising:

a first roller;

at least one additional roller;

a belt forming a closed loop, which belt is mounted on said first roller and said at least one additional roller;

at least one non-fixed abrasive chemical mechanical planarization polishing pad mounted to said belt, the non-fixed abrasive chemical mechanical planarization polishing pad configured to [adapted to] receive a polishing slurry, wherein the non-fixed abrasive chemical mechanical planarization polishing pad polishes a surface of the semiconductor wafer with the polishing;

and

a drive system coupled to at least said first roller to rotate said first roller and to cause said belt and said non-fixed abrasive chemical mechanical planarization polishing pad to move in a path;

wherein said belt is formed of metal.

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36. (Amended) A polishing pad assembly for polishing a semiconductor wafer, said assembly comprising:

a belt forming a closed loop; and

at least one non-fixed abrasive chemical mechanical planarization polishing pad mounted on the belt, the non-fixed abrasive chemical mechanical planarization polishing pad configured to [adapted to] receive a polishing slurry, wherein the non-fixed abrasive chemical mechanical planarization polishing pad polishes a surface of the semiconductor wafer with the polishing;

wherein said belt comprises a polyurethane material.

37. (Amended) A polishing pad assembly for polishing a semiconductor wafer, said assembly comprising:

a first roller;

at least one additional roller;

a belt forming a closed loop, which belt is mounted on said first roller and said at least one additional roller;

at least one non-fixed abrasive chemical mechanical planarization polishing pad mounted to said belt, the non-fixed abrasive chemical mechanical planarization polishing pad configured to [adapted to] receive a polishing slurry, wherein the non-fixed abrasive

chemical mechanical planarization polishing pad polishes a surface of the semiconductor wafer with the polishing;

and

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a drive system coupled to at least said first roller to rotate said first roller and to cause said belt and said non-fixed abrasive chemical mechanical planarization polishing pad to move in a path;

wherein said belt comprises a polyurethane material.

38. (Amended) A polishing pad assembly for polishing a semiconductor wafer, said assembly comprising:

a belt forming a closed loop; and

at least one non-fixed abrasive chemical mechanical planarization polishing pad mounted on the belt, the non-fixed abrasive chemical mechanical planarization polishing pad configured to [adapted to] receive a polishing slurry, wherein the non-fixed abrasive chemical mechanical planarization polishing pad polishes a surface of the semiconductor wafer with the polishing;

wherein said belt comprises a high-strength polymer.

40. (Amended) A polishing pad assembly for polishing a semiconductor wafer, said

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assembly comprising:

a first roller;

at least one additional roller;

a belt forming a closed loop, which belt is mounted on said first roller and said at least one additional roller;

at least one non-fixed abrasive chemical mechanical planarization polishing pad mounted to said belt, the non-fixed abrasive chemical mechanical planarization polishing pad configured to [adapted to] receive a polishing slurry, wherein the non-fixed abrasive chemical mechanical planarization polishing pad polishes a surface of the semiconductor wafer with the polishing;

and

a drive system coupled to at least said first roller to rotate said first roller and to cause said belt and said non-fixed abrasive chemical mechanical planarization polishing pad to move in a path;

wherein said belt comprises a high-strength material.